2SK2892-01R FUJI POWER MOSFET

Fuji Electric

[200509]

N-CHANNEL SILICON POWER MOSFET

FAP-IIIB SERIES

■ Features

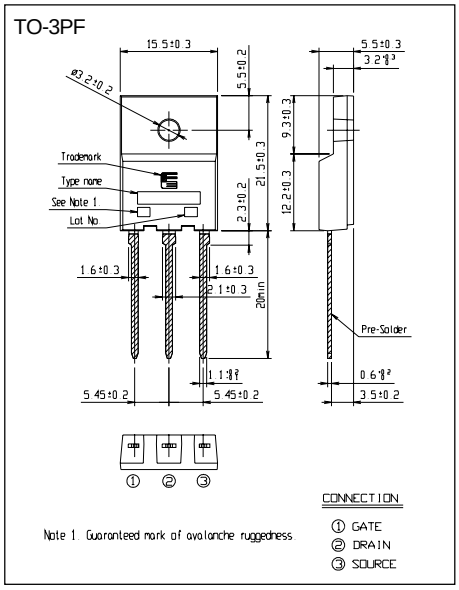
- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage
- Avalanche-proof

■ Applications

- Switching regulators
- DC-DC converters
- General purpose power amplifier

■ Outline Drawings

TO-3PF



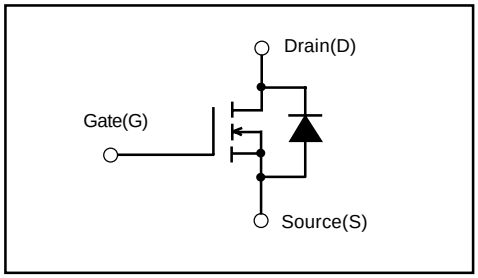
■ Maximum ratings and characteristics

● Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Rating	Unit	Remarks
Drain-source voltage	V_{DS}	30	V	
Continuous drain current	I_D	±90	A	
Pulsed drain current	$I_{D[puls]}$	±360	A	
Gate-source peak voltage	V_{GS}	±16	V	
Maximum avalanche energy	E_{AV}	1728.5	mJ	*1
Maximum power dissipation	P_D	100	W	
Operating and storage temperature range	T_{ch}	+150	℃	
	T_{stg}	-55 to +150	℃	

*1 L=0.285mH, Vcc=12V

■ Equivalent circuit schematic



● Electrical characteristics (T_c =25°C unless otherwise specified)

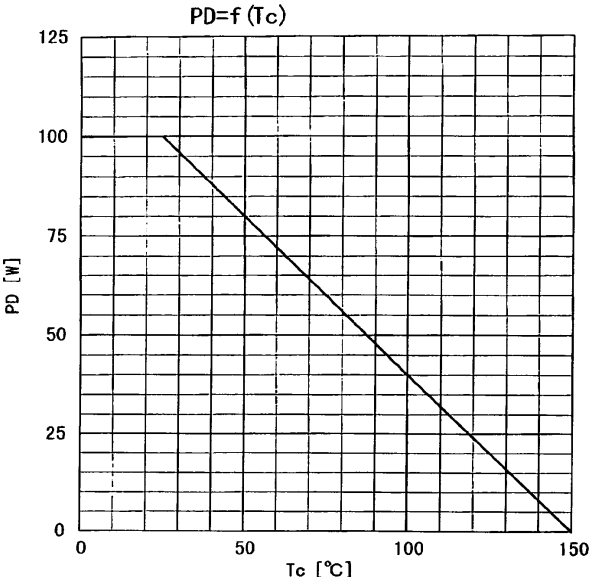
Item	Symbol	Test Conditions		Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D=1mA V_{GS}=0V		30			V
Gate threshold voltage	$V_{GS(th)}$	I_D=1mA V_{DS}=V_{GS}		1.0	1.5	2.0	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=30V V_{GS}=0V	T_{ch}=25°C		10	500	μA
			T_{ch}=125°C		0.2	1.0	mA
Gate-source leakage current	I_{GSS}	V_{GS}=±16V V_{DS}=0V			10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=50A V_{GS}=10V	V_{GS}=4V		7.0	9.5	mΩ
			V_{GS}=10V		4.4	5.5	mΩ
Forward transconductance	g_{fs}	I_D=50A V_{DS}=25V		35	70		S
Input capacitance	C_{iss}	V_{DS}=25V			3900	5850	pF
Output capacitance	C_{oss}	V_{GS}=0V			2000	3000	
Reverse transfer capacitance	C_{rss}	f=1MHz			850	1280	
Turn-on time	$t_{d(on)}$	V_{CC}=15V R_G=10 Ω			17	30	ns
	t_r	I_D=100A			70	110	
Turn-off time	$t_{d(off)}$	V_{GS}=10V			250	380	
	t_f				180	270	
Avalanche capability	I_{AV}	L=100μH T_{ch}=25°C		90			A
Diode forward on-voltage	V_{SD}	I_F=50A V_{GS}=0V T_{ch}=25°C			1.0	1.5	V
Reverse recovery time	t_{rr}	I_F=50A			65		ns
Reverse recovery charge	Q_{rr}	-di/dt=100A/μs T_{ch}=25°C			0.12		μC

● Thermal characteristics

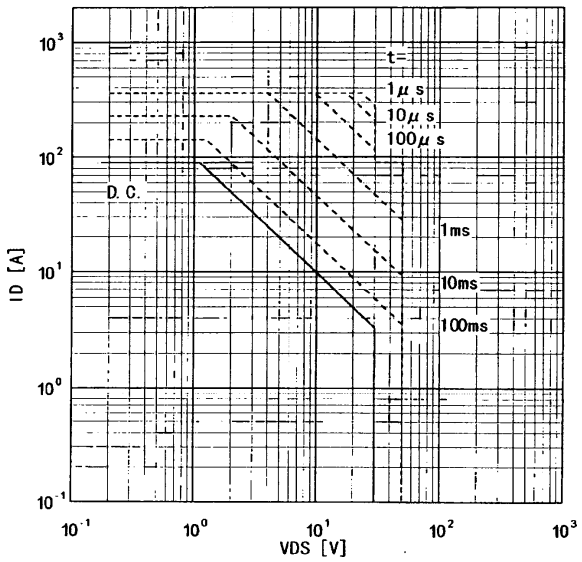
Item	Symbol	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$			1.25	°C/W
	$R_{th(ch-a)}$			30.0	°C/W

Characteristics

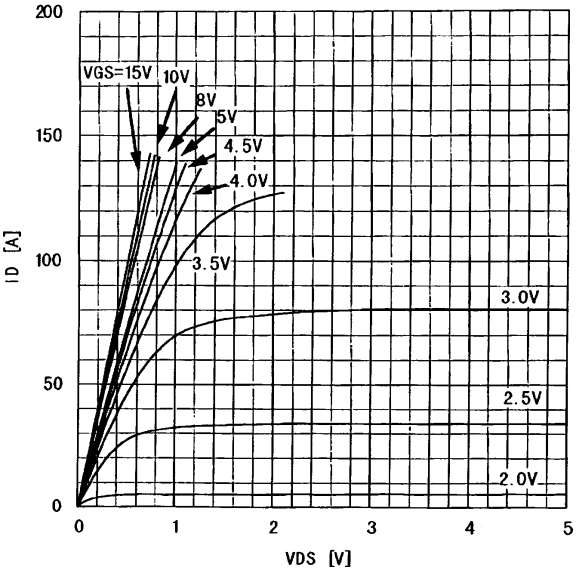
Power Dissipation
PD=f(Tc)



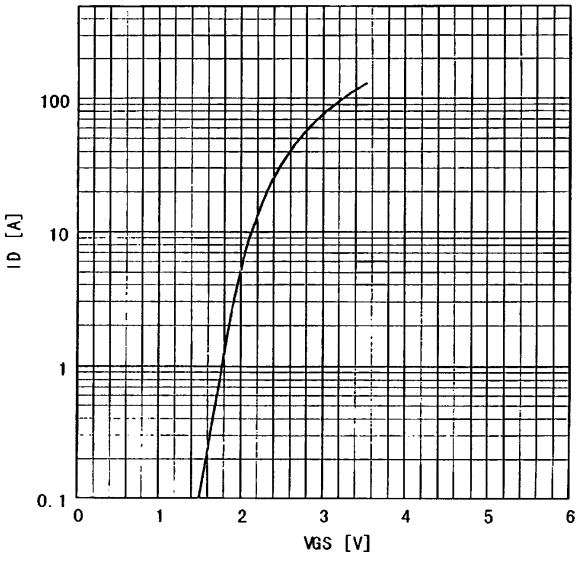
Safe operating area
ID=f(VDS) : D=0.01, Tc=25°C



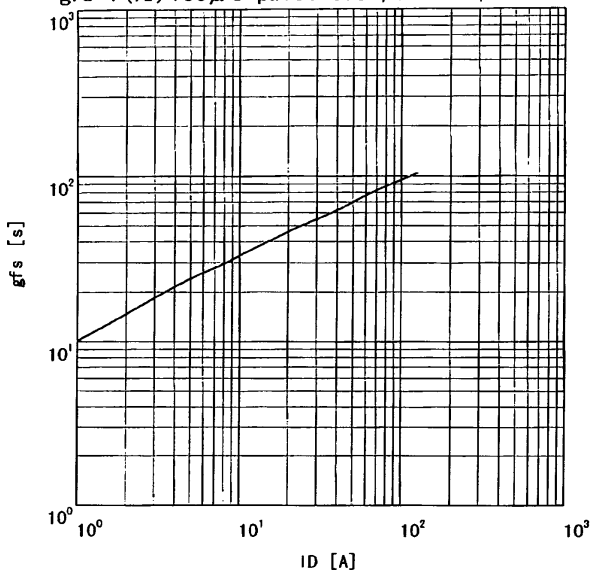
Typical output characteristics
ID=f(VDS) : 80μs pulse test, Tc=25°C



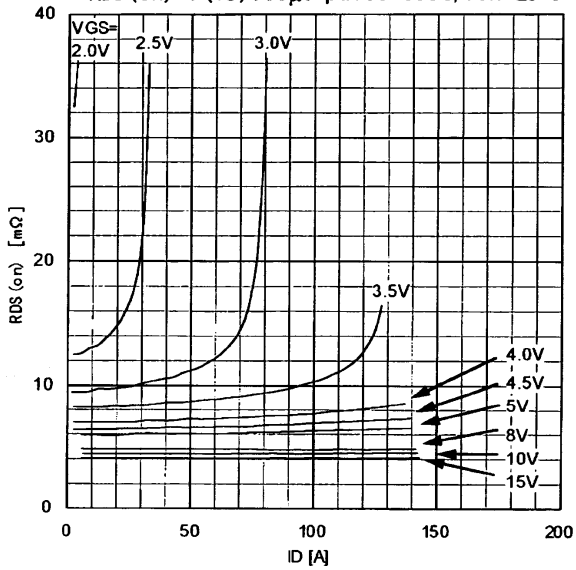
Typical transfer characteristics
ID=f(VGS) : 80μs pulse test, VDS=25V, Tch=25°C



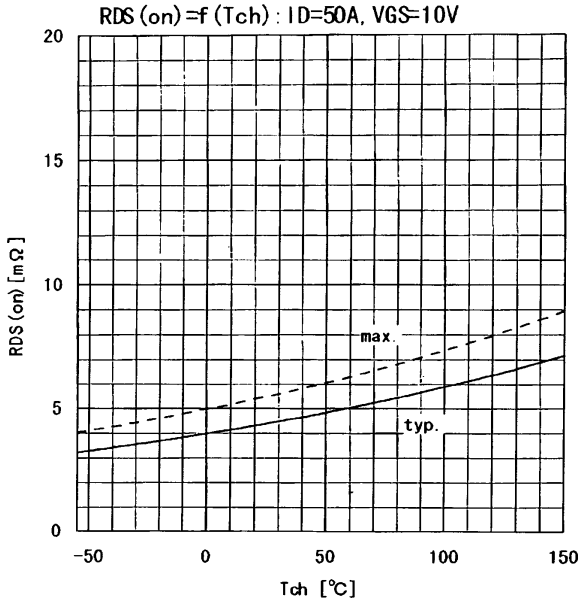
Typical forward transconductance
gfs=f(ID) : 80μs pulse test, VDS=25V, Tch=25°C



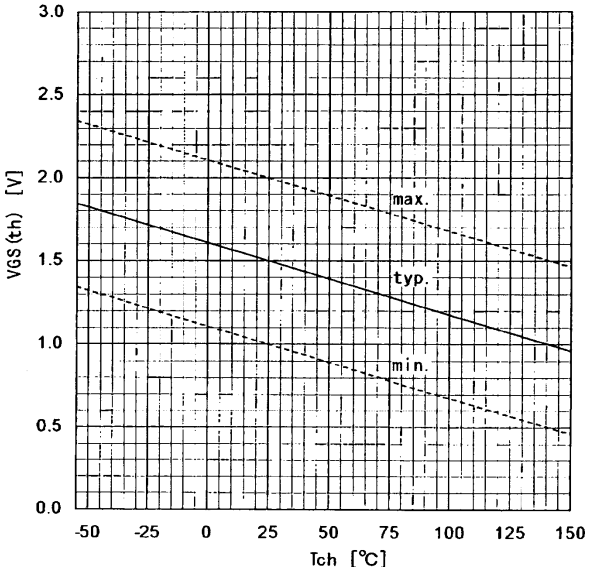
Typical Drain-Source on-State Resistance
RDS(on)=f(ID) : 80μs pulse test, Tch=25°C



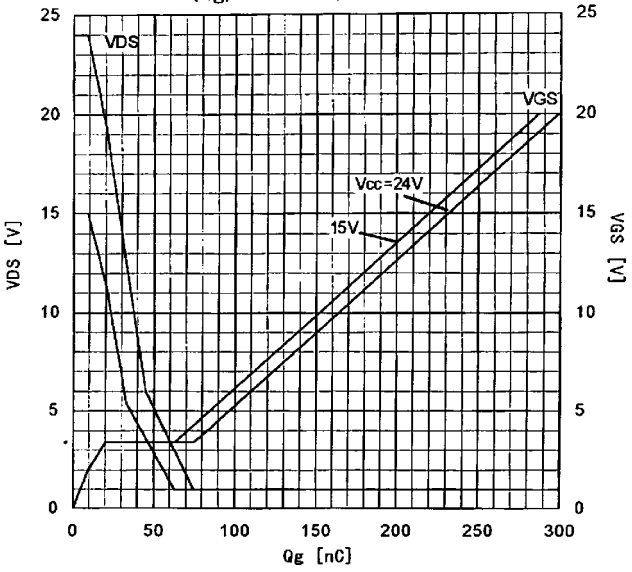
Drain-source on-state resistance
RDS(on)=f(Tch) : ID=50A, VGS=10V



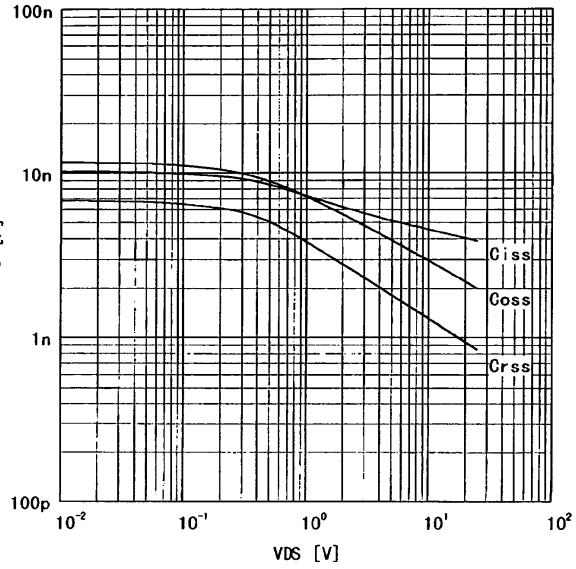
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch) : VDS=VGS, ID=1mA



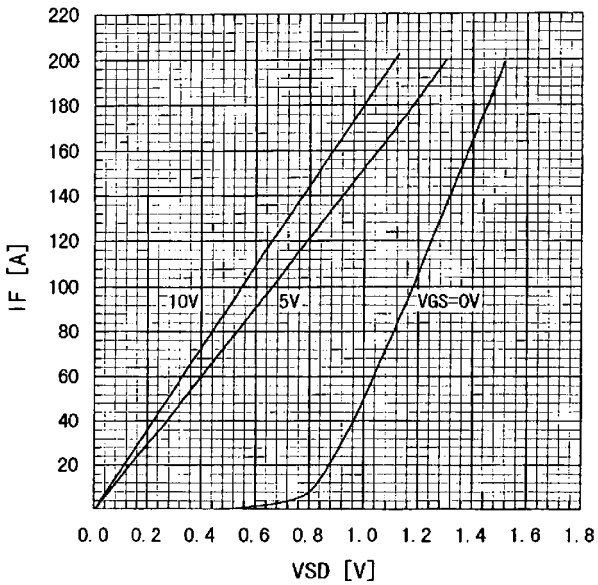
Typical Gate Charge Characteristics
VGS=f(Qg) : ID=100A, Tch=25°C



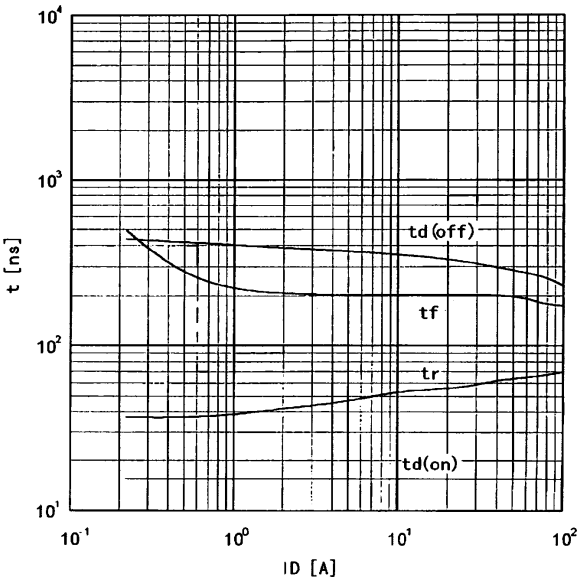
Typical capacitances
C=f(VDS) : VGS=0V, f=1MHz



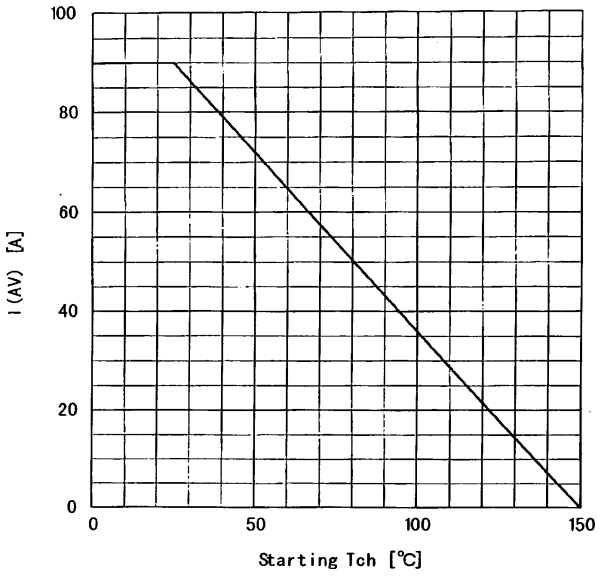
Typical Forward Characteristics of Reverse Diode
IF=f(VSD) : 80μs pulse test, Tch=25°C



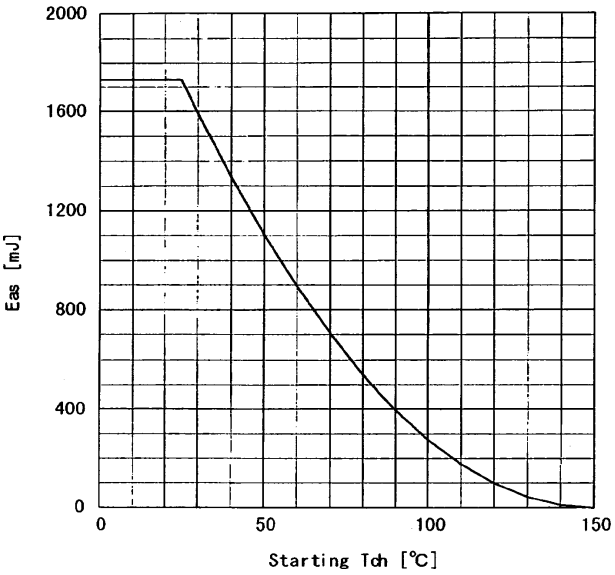
Typical Switching Characteristics vs. ID
t=f(ID) : Vcc=15V, VGS=10V, RG=10Ω



Maximum Avalanche Current vs. starting Tch
I(AV)=f(starting Tch)



Maximum Avalanche energy vs. starting Tch
Eas=f(starting Tch):Vcc=12V, I_{AV}≦90A



Transient thermal impedande
Zthch=f(t) parameter:D=t/T